



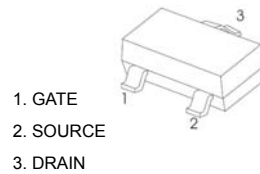
FEATURES

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

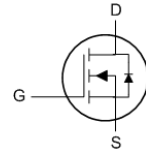
V_{DSS} 20 V
 I_D 6 A
 $R_{DS(ON)}$ 22 m Ω

2300

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Maximum Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

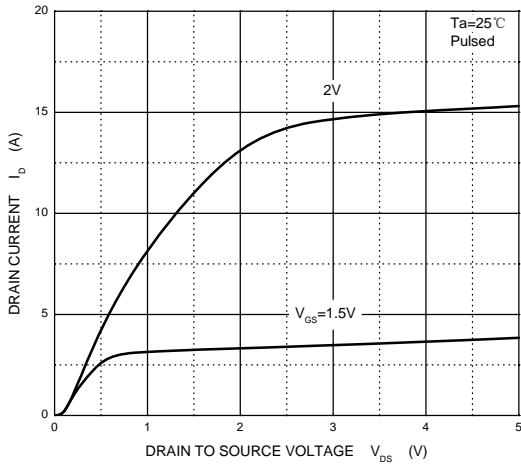
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate-source leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1.0	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 5.0A$		22	27	m Ω
		$V_{GS} = 2.5V, I_D = 4.0A$		35	42	
		$V_{GS} = 1.8V, I_D = 2.0A$			73	
Diode forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$		0.75	1	V
Forward transconductance	g_{fs}	$V_{DS} = 5V, I_D = 3.8A$	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 5V, V_{DS} = 10V,$ $R_L = 1.7\Omega, R_{GEN} = 6\Omega$		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{d(off)}$			29		
Fall time	t_f			10.2		

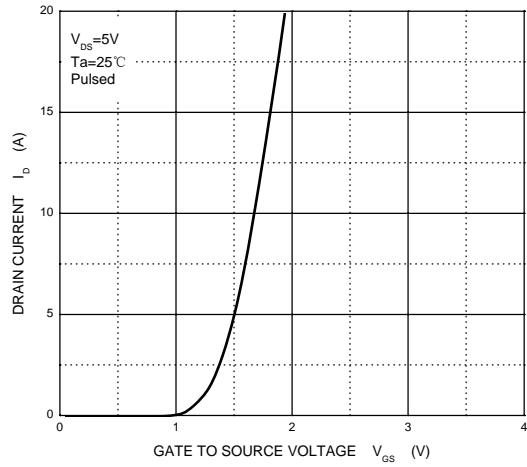
*These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES

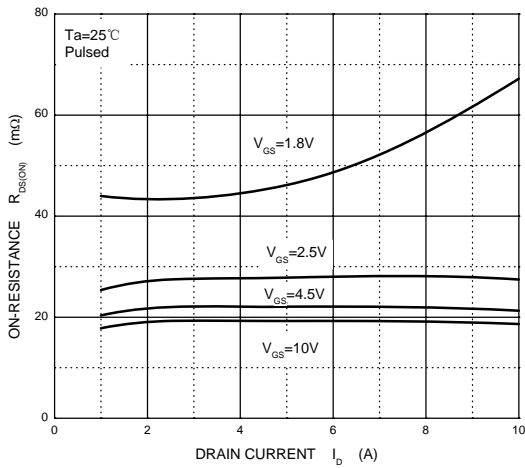
Output Characteristics



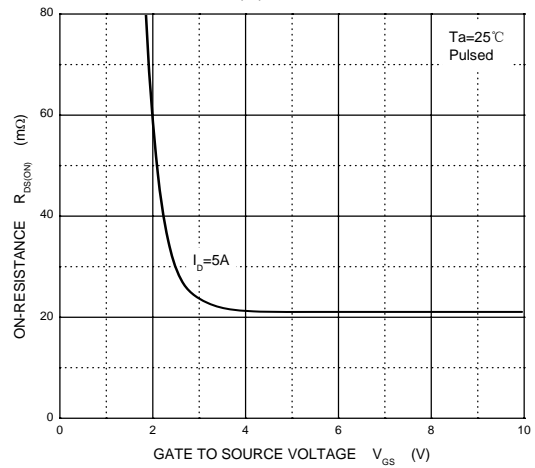
Transfer Characteristics



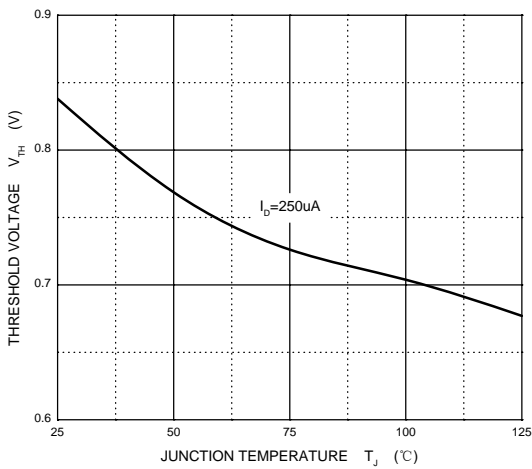
$R_{DS(ON)}$ — I_D



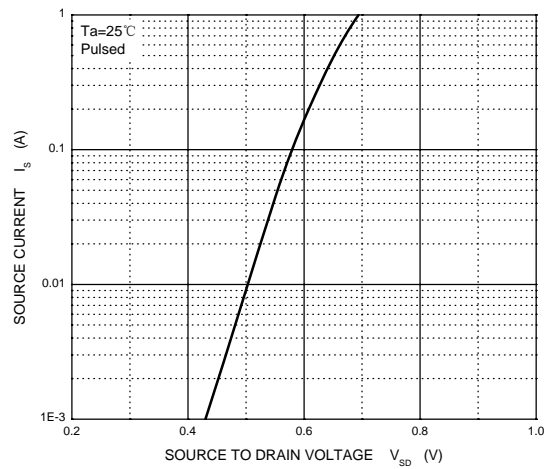
$R_{DS(ON)}$ — V_{GS}



Threshold Voltage



I_S — V_{SD}



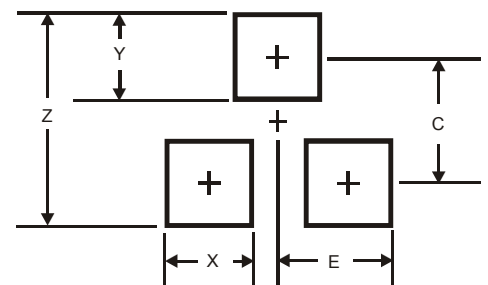
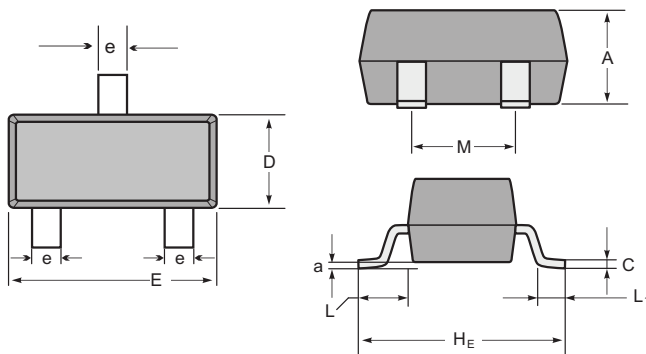
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23



SOT-23 mechanical data

UNIT	A	C	D	E	HE	e	M	L	L1	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.10
		P1	4.00±0.10
		P2	2.00±0.10
		D0	1.55±0.10
		D1	1.05±0.10
		E	1.55±0.10
		F	3.60±0.10
		W	8.00±0.10
		A0	3.80±0.20
		B0	3.25±0.20
		K0	1.45±0.10
		T	0.25±0.05
		D2	178.0±3.0
		D3	55Min.
		D4	R24.0±3.0
G	R82.0±3.0		
I	13.0±2.0		
W1	11.0±3.0		
Quantity: 3000PCS			

7" Reel	